

View Online at https://aerobasegroup.com/nsn/5961-00-361-8767

Inclosure	Material:
Metal	
Overall L	ength:
0.260 inch	nes
Terminal	Length:
0.500 inch	nes
Overall D	iameter:
0.370 inch	nes
Compone	ent Name And Quantity:
2 transisto	n
Mounting	g Method:
Terminal	
Terminal	Circle Diameter:
0.200 inch	nes
Features	Provided:
Hermetica	ally sealed case
Semicon	ductor Material:
Silicon all	transistor
Voltage R	Rating In Volts Per Characteristic:
-90.0 bre	akdown voltage, gate-to-source, with all other terminals short-circuited to source all transistor and -35.0 breakdown voltage,
drain-to-se	ource, with all other terminals short-circuited to source all transistor and -6.0 gate to source threshold voltage all transistor
Current F	Rating Per Characteristic:
-10.00 nai	noamperes zero-gate-voltage drain current all transistor and -1.00 nanoamperes reverse gate current with all other terminals
short-circu	uit to source, junction-gate all transistor
Maximum	n Operating Tempurature Per Measurement Point:
125.0 deg	rees celsius junction
Precious	Material And Location:
Leads gol	d
Precious	Material:
Gold	
Terminal	Type And Quantity:
8 uninsula	ated wire lead
Shelf Life	2:
N/a	
Unit Of M	leasure:
Demilitar	ization:
No	
Fiig:	
A110a0	